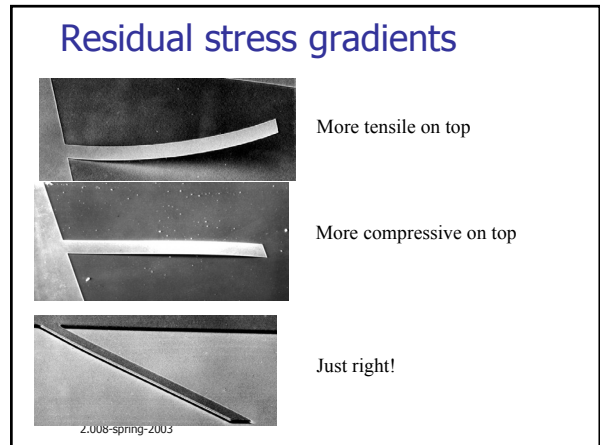


### Surface micromachining

Structure	sacrificial	etchant
■ Polysilicon	Silicon dioxide	HF
■ SiNx	PSG	HF
■ Silicon dioxide	polysilicon	XeF2
■ SiNx	polysilicon	XeF2
■ Aluminum	photoresist	oxygen plasma

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### Clean Room

- Gowning with bunny suit
- Class 1, 10, 100

**working in a cleanroom**

- Salt made of ultra clean material
- Wettable pack for air filter systems
- at points of pressure regain & losses
- in places of fast gear changeable slow recovery & under hood
- Metal insulation air filter suit
- Will also protect & monitor cleanliness
- Work

A salt grain on a chip

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### Class of clean rooms

- Class 1 means one speckle of 0.5  $\mu$  partical in one ft<sup>3</sup>.
- Class 10, 100, 1000
- HEPA filter, AHU

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## Air Filters

- HEPA (High Efficiency Particulate Air) filters
- High efficiency, low  $\Delta p$ , good loading characteristics
- Glass fibers in a paper like medium
- 97% retainment of incident particles of 0.3  $\mu\text{m}$  or larger

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## Class of clean rooms

Class	0.5 $\mu$ particle	Temp tolerance	RH tolerance	\$/ft <sup>2</sup>
10,000	10,000	+/- 3°F	+/- 5%	\$250-300
1,000	1,000	+/- 2°F	+/- 5%	\$350-400
100	100	+/- 1°F	+/- 5%	\$1200
10	10	+/- 0.5°F	+/- 3%	\$3500
1	1	+/- 0.3°F	+/- 2%	\$10,000

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## Particles

class	0.1 $\mu$	0.2 $\mu$	0.3 $\mu$	0.5 $\mu$	5.0 $\mu$
1	35	7.5	3	1	N/A
10	350	75	30	10	N/A
100	N/A	750	300	100	N/A
1000	N/A	N/A	N/A	1000	7

Federal Standard 209; Number of particles per cubic foot

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## Toxicity

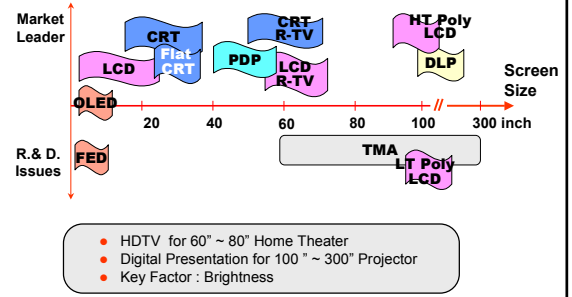
- TLV (Threshold Limit Value)
  - Upper limit material concentration that an average healthy person can be exposed without adverse effects, ppm or mg/m<sup>3</sup>
- Notorious Poisons
  - CO (100 ppm), CO<sub>2</sub> (5000 ppm), HCN (110 ppm), H<sub>2</sub>S (10 ppm)
  - SO<sub>2</sub> (5 ppm), NH<sub>3</sub> (50 ppm)
  - Arsenic trioxide AS<sub>2</sub>O<sub>3</sub> (0.1g fatal)
  - Hg (0.1 ppm via skin contact)
  - All material are toxic in sufficient quantity, 5g caffeine is fatal.

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## MEMS Applications

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## Display Technologies



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## Brightness of Projection Displays

1995  
 CRT : ~300 lm  
 LCD : ~600 lm  
 ? : ~2000 lm

$\text{lux} = \text{lumen} / \text{m}^2$

**1<sup>st</sup> Optical MEMS device** PHOTONICS AND MICROMACHINING

### DIGITAL MICROMIRROR DEVICE & DLP PROJECTOR

9335-29 CORPORATE RESEARCH & DEVELOPMENT

## DMD Optical Switching Principle

DMD Mirror on/off  $\pm 10^\circ$

Texas Instruments's Technical Journal: Vol. 15, No. 3, July-Sept. 1998.

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## DMD Cell Structure

Texas Instruments's Technical Journal: Vol. 15, No. 3, July-Sept. 1998.

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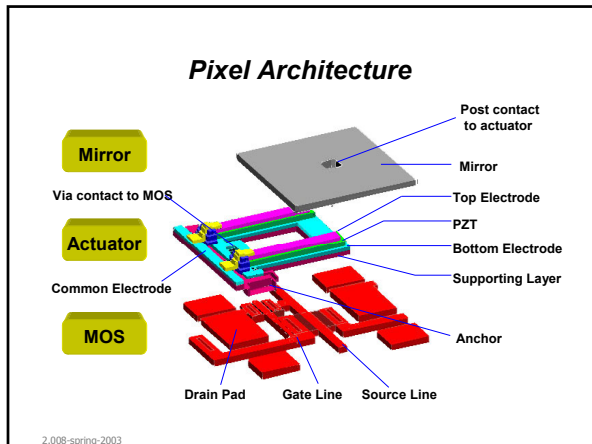
## TMA

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## Light Modulation of TMA

### Thinfilm Micromirror Array

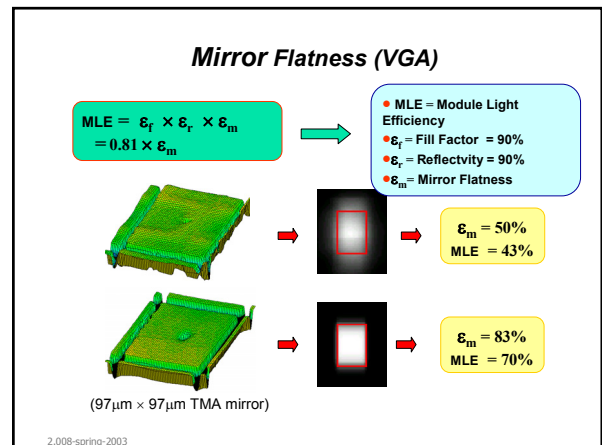
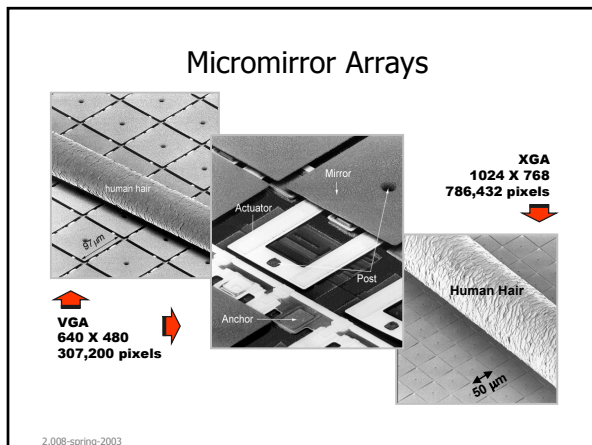
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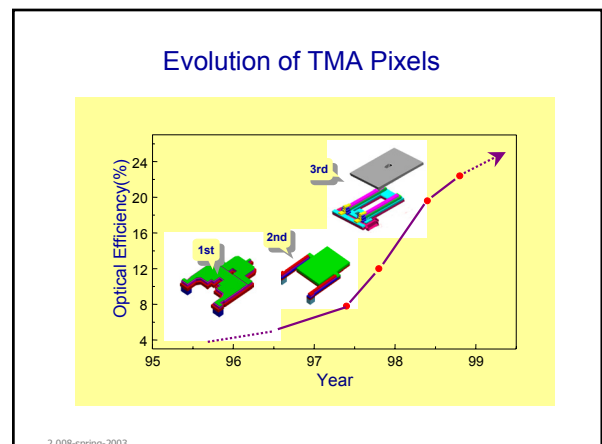
### TMA vs DMD

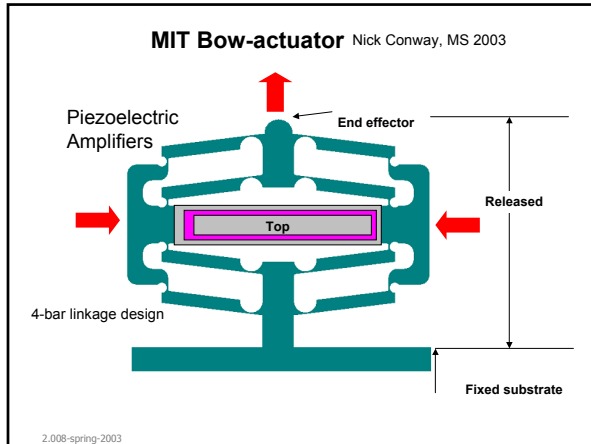
	DMD™ (Texas Instrument) Electrostatic	TMA™ (Daewoo Electronics) Piezoelectric
Actuation	Electrostatic	Piezoelectric
Tilting Angle	-10°, 0°, +10°	0° ~ 3° (continuous)
Gray Scale Control	On/Off Complex	Linear Simple
Drawbacks	<ul style="list-style-type: none"> <li>Fatigue</li> <li>Sticking</li> <li>High Cost</li> </ul>	<ul style="list-style-type: none"> <li>Uniformity</li> </ul>

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- ### Coupled Natures of Thin Film Processes
- Forward coupling
    - Step coverage, conformality
  - Backward coupling
    - Temperature dependent microstructural degradation
    - Over/under etch, etch stop control
    - Side attack, Passivation breakage
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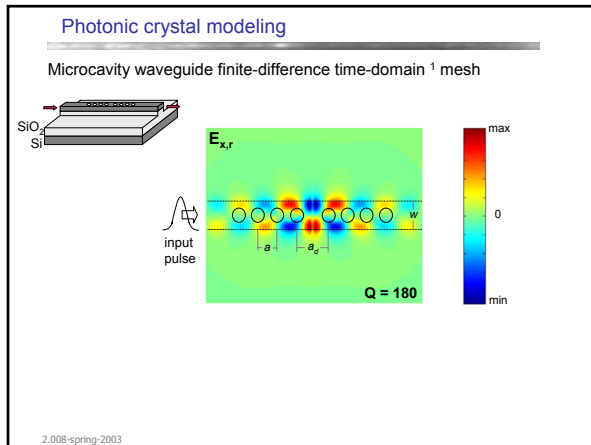


### Design of nanopipette (2): In-line array of nanopipettes

- Massive Parallel Nanopipette Array by In-plane Scanning Probe Systems
- Integration with Microfluidic channels
- Integration of nanopipettes in AFM in an 100 x 100 array

Single nanopipette

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### Photonic band gap microcavity waveguide processing

- design matrix of various geometries: defect lengths, waveguide width,  $d/a$ , number of holes
- Nanofabrication:
  - $\text{SiN}_x$  mask<sup>1</sup> /w electron-beam
  - Proximity pattern transfer to resist
  - 130 nm minimum features
  - Hard mask from Cr lift-off<sup>2</sup>
  - Optimized Si RIE

2.008-spring-2003 <sup>1</sup>J. Ferrera, NanoStructures Laboratory, MIT. <sup>2</sup>J. Foresi, Kimerling group, MIT.

